# AI + Materials Science

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Image from: DeepMind

#### Outlines

- Intro to Materials Science
  - Crystalline Materials
  - Structure-Property Relationship
  - DFT Calculation
- Al in Materials Science
  - Artificial intelligence ab initio (Al<sup>2</sup>) methods
  - Directly Bridging
  - Inverse Problem
  - Al as a Powerful Assistance
  - Outside and Beyond Crystals

#### What are Materials?

- Fundamental building blocks of modern life
- Every piece of solid thing you can touch around you
- The history of human civilization is also the history of how humans exploit different kinds of materials



## Why do we Care about Materials?

#### • Necessity:

- Everything is made out of something
- Materials selection is critical to design and performance

#### • Ambition:

- New materials = new opportunities
- Ex: transistor to integrated circuit

• Fear:

- Most failures are materials failures
- Ex: aircraft accident due to material fracture



Vacuum Tube

MOSFET

## Classification of Materials: Two Categories

Fundamental difference: Long-range Order of Atoms

- Crystalline Materials:
  - Atoms are arranged in a periodic pattern repeated throughout the material
  - Ex: diamond, most of semiconductors and metals



#### • Amorphous Materials:

- No systematic and regular pattern of atom arrangements
- Ex: glass, plastic, rubber



Generally speaking:

• Most of crucial functional applications rely on crystalline materials

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# Intro to Materials Science

**Crystalline Materials** 



- Periodic repeating pattern of atoms can be clearly observed
- But how to properly describe such structures?

Atomic Resolution TEM HAADF Image of Crystalline Material [1] [1] Mazet, L., et al. (2015). A review of molecular beam epitaxy of ferroelectric  $BaTiO_3$  films on Si, Ge and GaAs substrates and their applications. *Science and Technology of Advanced Materials*, *16*(3).



- Fundamental Truth:
  - The crystal consists of identical atom groups as minimal repeating units
  - The crystal is constructed by duplicating its repeating unit following a **certain pattern**

Atomic Resolution TEM HAADF Image of Crystalline Material



Atomic Resolution TEM HAADF Image of Crystalline Material



- Minimal repeating unit:
  - Unit Cell
  - The position of each atom is described by a fractional coordinate in the cell:
  - Ex: Ti atom at the body center

$$\overrightarrow{\mathbf{T}\mathbf{i}} = \left[\frac{1}{2}, \frac{1}{2}, \frac{1}{2}\right]^{\mathrm{T}}$$

• Ex: O atom at the top center

$$\vec{\mathbf{0}} = \left[\frac{1}{2}, \frac{1}{2}, 1\right]^{\mathrm{T}}$$





- Minimal repeating unit:
  - Unit Cell

Each Unit Cell can be abstracted as a blue dot in the Lattice Grid

- Repeating pattern:
  - Lattice Grid



#### Lattice Grid:

 Similar to the Cartesian coordinate system, defined by a set of basis
 Lattice Vectors:

 $l_1, l_2, l_3$ 

• The angles between lattice vectors is defined as **lattice angles**:

 $\alpha, \beta, \gamma$ 

 Together, they are defined as Lattice Constant

()

 $\boldsymbol{l}_2$ 

 $l_3$ 

• In our example: Cubic BaTiO<sub>3</sub>

$$||\vec{a}|| = ||\vec{b}|| = ||\vec{c}|| = 4.01 \text{ Å}$$
$$\alpha = \beta = \gamma = 90^{\circ}$$

- Ps. 1 Å = 0.1 nm
- Mathematically, structure of a crystalline material  $\mathcal{M}$  can be represented as:  $\mathcal{M} = (A, X, L)$ 
  - $A \in \mathbb{Z}^n$ : vector of atomic numbers of n atoms in the Unit Cell
  - $X = [x_1, x_2, ..., x_n] \in \mathbb{R}^{3 \times n}$ : tensor of fractional atom coordinates
  - $L = [l_1, l_2, l_3] \in \mathbb{R}^{3 \times 3}$ : tensor of Lattice Vectors
- Given the Unit Cell, repeat along the Lattice Vectors, you are now able to reconstruct the ENTIRE crystal!

## Crystalline Materials: $\mathcal{M} = (A, X, L)$



- $X = [x_1, x_2, ..., x_n] \in \mathbb{R}^{3 \times n}$ : tensor of fractional atom coordinates
- $L = [l_1, l_2, l_3] \in \mathbb{R}^{3 \times 3}$ : tensor of Lattice Vectors
- Crystal structure  $\mathcal{M}$  has properties as follow:
  - **Real space** coordinates *C* of atoms can be obtained as:

$$\boldsymbol{C}^{\mathrm{T}} = \boldsymbol{X}^{\mathrm{T}} \cdot \boldsymbol{L}$$

• Periodicity:

 $l_3$ 

$$\begin{aligned} \mathbf{x}'_i &= \mathbf{x}_i + \mathbf{t} \cdot \mathbf{L} \\ \mathbf{t} \in \mathbb{Z}^3 \end{aligned}$$

• coordinates of atoms with same index *i* in the periodic expanded space can be obtained by adding a combination of integer multiple lattice vectors

#### Crystal Structures:

- 7 crystal systems and 14 Bravais lattices
- spatial arrangement of atoms determines the material properties



# Intro to Materials Science

## The Essence of Materials Science

• The fundamental research subject can be summarized as:

- Structure:
  - **Composition**: kind and fraction of atoms present
  - Microstructure: how those atoms are arranged in the materials
- Property:
  - Isotropic: orientation-irrelevant, e.g. density, heat capacity, melting point
  - Anisotropic: e.g. polarity, magnetization, piezoelectricity

- Ex: Piezoelectric ceramics BaTiO<sub>3</sub>
- Structure:
  - **Composition**: Ba:Ti:O = 1:1:3
  - Microstructure: described as Fig.a
- Property:
  - Isotropic:
    - density =  $6.02 \text{ g/cm}^3$ ,
    - melting point = 1,625 °C
  - Anisotropic:
    - piezoelectricity along the polarization (z-axis in Fig.b)





## **Experimental Approaches** Preparation Experiments Material (Shape-memory heart stent) Properties Structure

#### Experimental Approaches





### Experimental Approaches



Structure

- Limitations:
  - Desired structure can not be prepared with precise, atomiclevel control
  - Property of many structures worth studying is unable to be determined experimentally
  - High experimental costs and low efficiency

## Theoretical Approaches





Energy

- The valence band of Si is fully filled and the conduction band is empty, preventing the electrons from traveling through the material
- The electrons need to be excited across the band gap by thermal or external energy
- Therefore, the conductivity of Si at temperature T can be approximated:  $\sigma \approx N_0 e \mu_e \exp \frac{(E_G)}{kT}$
- Here  $N_0$  is number of electrons per unit volume,  $\mu_0$  is the carrier mobility of electron

X Band Structure of Intrinsic Semiconductor (Si)

### Theoretical Approaches





- Limitations:
  - Lots of assumptions and approximations have to be applied to the theory
  - Ignored some of the complex micro-scale interactions
  - Limited application scenarios

Band Structure of Intrinsic Semiconductor (Si)

# Intro to Materials Science

**DFT Calculation** 

#### Computational Approaches

- Can we try to compute the material properties purely from its structures?
  - *Ab initio* Calculations: from electrons to properties
- Wave Function of electron:

 $\Psi(\boldsymbol{r},t)$ 

• Probability Density:

$$\Psi^*(\boldsymbol{r},t)\Psi(\boldsymbol{r},t) = |\Psi(\boldsymbol{r},t)|^2$$

e

 ${}^{1}_{1}H$ 

• Schrödinger Equation:

$$\widehat{H}\Psi(\boldsymbol{r},t) = i\hbar \frac{\partial}{\partial t}\Psi(\boldsymbol{r},t)$$

• where the Hamiltonian operator is:

$$\widehat{H} = -\frac{\hbar^2}{2m}\nabla^2 + \widehat{V}$$

• Time-Independent Schrödinger Equation:

$$\widehat{H}\psi(\boldsymbol{r}) = E\psi(\boldsymbol{r})$$
  
 $E_1, \psi_1;$ 

#### Ab initio Calculations: Schrödinger equation

- Works fine for single electron system: H atom, hydrogenic ions (He<sup>+</sup>, Li<sup>2+</sup>)
- Directly solving the many-electron Schrödinger equation is currently computationally impossible, with complexity exponential to N, the number of electrons in the system
- Schrödinger Equation:

$$\widehat{H}\Psi(\boldsymbol{r},t) = i\hbar \frac{\partial}{\partial t}\Psi(\boldsymbol{r},t)$$

• Many-Body Calculation:

$$\widehat{H}\psi(\mathbf{R}) = \left[\widehat{T} + \widehat{V} + \widehat{U}\right]\psi(\mathbf{R}) = E\psi(\mathbf{R})$$
$$\left[\sum_{i=1}^{N} \left(-\frac{\hbar^2}{2m_i}\nabla_i^2\right) + \sum_{i=1}^{N} V(\mathbf{r}_i) + \sum_{i\neq j}^{N} U(\mathbf{r}_i, \mathbf{r}_j)\right]\psi = E\psi$$



#### Ab initio Calculations: Hartree-Fock Method

- Hartree-Fock Method (HF): Self-Consistent Field (SCF)
- Assuming each electron is in an average potential field generated by all the other electrons:

- Hohenberg-Kohn (HK) Theorems:
- Electron Density:

$$\rho_0(\boldsymbol{r}) = N \int d\boldsymbol{r}_1 \dots \int d\boldsymbol{r}_N \psi_0^*(\boldsymbol{R}) \psi_0(\boldsymbol{R})$$

• Total Energy:

$$E_0(\rho_0) = \psi_0^*(\rho_0)\widehat{H}\psi_0(\rho_0)$$

• HK Theorems proof: <a href="https://people.chem.ucsb.edu/metiu/horia/OldFiles/115C/KH\_Ch4.pdf">https://people.chem.ucsb.edu/metiu/horia/OldFiles/115C/KH\_Ch4.pdf</a>

### Ab initio Calculations: DFT

- Density Functional Theory (DFT):
  - Assumes that the property of the system is determined by electron density ho
  - Treats the **energy as the functional of electron density** (3 variables), instead of trying to solve the entire wave function in the Schrödinger Equation (Nx3 variables)
  - The target of DFT calculation is to solve the Kohn-Sham equation:

$$-\frac{\hbar\nabla^2}{2m} + v_{\rm KS}[\rho](\boldsymbol{r})\right)\varphi_i(\boldsymbol{r}) = \varepsilon_i\varphi_i(\boldsymbol{r})$$

• Where  $\rho$  is defined in terms of the Kohn-Sham wave functions  $\varphi_i$ :

$$\rho(\mathbf{r}) = \sum_{i} |\varphi_i(\mathbf{r})|^2$$





Walter Kohn

Lu Jeu Sham

## Ab initio Calculations: DFT

- Density Functional Theory (DFT):
- The Kohn-Sham potential  $v_{\rm KS}$  consists of 3 terms:
  - External potential  $v_{\rm ext}$ : generated by the nucleus
  - The Hartree potential  $v_{\text{Hartree}}$ : the Coulomb repulsion between electrons
  - Exchange-correlation potential  $v_{\rm xc}$ : complex quantum mechanical interactions

$$v_{\text{KS}}[\rho](\boldsymbol{r}) = v_{\text{ext}}(\boldsymbol{r}) + v_{\text{Hartree}}[\rho](\boldsymbol{r}) + v_{\text{xc}}[\rho](\boldsymbol{r})$$

#### The Nobel Prize in Chemistry 1998



Photo from the Nobel Foundation archive. Walter Kohn

Photo from the Nobel Foundation archive. John A. Pople

Similar to the H-F method, DFT applies self-consistency (SC) calculation:

- 1. Initialize electron density  $\rho_0(\mathbf{r})$  to start the iterative procedure
  - In principle, any random positive function normalized to the total number of electrons is acceptable
  - A reasonable initiation can speed up convergence, e.g.:

$$\rho_0(\boldsymbol{r}) = \sum_{\alpha} \rho_\alpha(\boldsymbol{r} - \boldsymbol{R}_{\alpha})$$

• Where  $R_{\alpha}$  and  $\rho_{\alpha}$  represents the position and atomic density of the nucleus

- 2. Calculate Kohn-Sham potential  $v_{\text{KS}} = v_{\text{ext}} + v_{\text{Hartree}} + v_{\text{xc}}$ :
  - The **external potential**  $v_{\text{ext}}$  is typically the sum of nuclear potentials:

$$v_{\text{ext}}(\boldsymbol{r}) = \sum_{\alpha} v_{\alpha}(\boldsymbol{r} - \boldsymbol{R}_{\alpha})$$

• Where  $v_{\alpha}$  can be the Coulomb potential with the nuclear charge  $Z_{\alpha}$ :

$$v_{\alpha}(\mathbf{r}) = -\frac{Z_{\alpha}}{r}$$

• Or use other predefined pseudo-potentials for  $v_{\alpha}$  depending on systems and tasks

- 2. Calculate Kohn-Sham potential  $v_{\rm KS} = v_{\rm ext} + v_{\rm Hartree} + v_{\rm xc}$ :
  - The Hartree potential  $v_{\text{Hartree}}$  can be calculated by either direct integration:

$$v_{\text{Hartree}}(\mathbf{r}) = \int \frac{\rho(\mathbf{r}')}{|\mathbf{r} - \mathbf{r}'|} d^3 \mathbf{r}'$$

• Or solving Poisson's equation:

$$\nabla^2 v_{\text{Hartree}}(\mathbf{r}) = -4\pi\rho(\mathbf{r})$$

- 2. Calculate Kohn-Sham potential  $v_{\rm KS} = v_{\rm ext} + v_{\rm Hartree} + v_{\rm xc}$ :
  - The exchange-correlation potential  $v_{\rm xc}$  consists of all the other non-classical interactions between electrons, defined as functional derivative of exchange-correlation energy:

$$\mathcal{P}_{\mathrm{XC}}[\rho](\mathbf{r}) = \frac{\delta E_{\mathrm{XC}}}{\delta \rho(\mathbf{r})}$$

• The exchange-correlation energy  $E_{\rm xc}$  can be calculated with different designs and approximations, for example the simplest local-density approximation (LDA):

$$E_{\rm xc} = \int d^3 \boldsymbol{r} \, \varepsilon^{\rm HEG} \big( \rho(\boldsymbol{r}) \big)$$

• Where  $\varepsilon^{\text{HEG}}(\rho)$  is the exchange-correlation energy per unit volume of homogeneous electron gas (HEG) of a given density  $\rho$ , which can be tabulated for different densities

3. Solving the Kohn-Sham equation:

$$\begin{pmatrix} -\frac{\hbar\nabla^2}{2m} + v_{\rm KS}[\rho](\boldsymbol{r}) \\ \widehat{H}_{\rm KS}\varphi_i(\boldsymbol{r}) = \varepsilon_i\varphi_i(\boldsymbol{r}) \end{pmatrix} \varphi_i(\boldsymbol{r}) = \varepsilon_i\varphi_i(\boldsymbol{r})$$

• Where  $\hat{H}_{\rm KS} = -\frac{\hbar \nabla^2}{2m} + v_{\rm KS}[\rho](\mathbf{r})$  is the Kohn-Sham Hamiltonian operator

• Apply the Hamiltonian operator to the basis set  $\{\phi_i(r)\}$  to obtain Hamiltonian matrix  $H_{\text{KS}}$ :  $H_{ij} = \int \phi_i^*(r) \widehat{H} \phi_j(r) dr$
# Density Functional Theory (DFT): Step 3

- 3. Solving the Kohn-Sham equation:
- The Hamiltonian matrix  $H_{KS}$  is an  $N \times N$  symmetrical matrix
- N is the total number of basis functions, with the basic assumption in DFT that the Kohn-Sham wave function is the **linear combination** of the basis set  $\{\phi_i(r)\}$ :

$$\varphi_i(\boldsymbol{r}) = \sum_j c_{ij} \phi_j(\boldsymbol{r})$$

- Where  $c_{ij}$  is the are the coefficients of the basis functions in the expansion of the ith Kohn-Sham wave function  $\varphi_i$
- Thus, each element  $H_{ij}$  in the  $H_{\rm KS}$  describes the interaction between basis  $\phi_i$  and  $\phi_j$

# Density Functional Theory (DFT): Step 3

- 3. Solving the Kohn-Sham equation:
- Once the Kohn-Sham Hamiltonian matrix  $H_{\rm KS}$  is constructed, the Kohn-Sham equations turned into an eigenvalue problem:

$$\boldsymbol{H}_{\mathrm{KS}}\boldsymbol{C}=\boldsymbol{E}\boldsymbol{C}$$

- where C is the matrix of coefficients, and E is the diagonal matrix of eigenvalues (orbital energies)
- Then, the Kohn-Sham wave functions can be constructed using *C* and basis set:

$$\varphi_i(\mathbf{r}) = \sum_j c_{ij} \phi_j(\mathbf{r})$$

### Density Functional Theory (DFT): Step 4&5

4. Calculate new electron density from obtained wave functions:

$$\rho_1(\mathbf{r}) = \sum_i |\varphi_i(\mathbf{r})|^2$$

- 5. Compare  $\rho_1(\mathbf{r})$  and initial guess  $\rho_0(\mathbf{r})$ :
- If the difference between two densities is lower than a user-defined criterion  $\eta$ :  $|\rho_1(r)-\rho_0(r)|<\eta$
- The calculation is considered as **self-consistent**
- With correctly calculated form of wave functions and Hamiltonian matrix, several observables can be evaluated, including total energy, band structure, conductivity, etc.

# Density Functional Theory (DFT): Iteration

- 6. If the convergence criterion has not been reached:
- A new iteration begins with  $ho_0'(r)$  of several different options:
  - A random guess again
  - Use the output of the previous cycle: always leads to instabilities
  - Mix the last output and the original input:

 $\rho_0'(\boldsymbol{r}) = \beta \rho_0(\boldsymbol{r}) + (1-\beta)\rho_1(\boldsymbol{r})$ 

- The mixing parameter  $\beta$  is typically chosen to be around 0.3
- Other mixing strategies similar to the one above
- Repeat step 2 to 5 until converged, highly dependent on calculation conditions and hyperparameters



# Density Functional Theory (DFT): Limitations



# Density Functional Theory (DFT): Limitations

- DFT calculation is still computationally expensive
- Especially for large-scale structures consists 10<sup>3</sup> atoms





Alloy



Defects



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# Al in Materials Science

Artificial intelligence ab initio (Al<sup>2</sup>) methods

# Deep Learning Approaches: Data Driven



Deep Potential Molecular Dynamics (DPMD):



- In each frame of the ab initio molecular dynamics

   (AIMD) simulation, the potential surface
   E(R<sub>1</sub>, R<sub>2</sub>, ..., R<sub>N</sub>) of the structure is determined
   through Quantum Mechanics (QM) calculation, where
   the R<sub>i</sub> is the coordinates of the atom i
- The **forces** on each atom can be calculated as the negative derivative of potential to the coordinates:

$$\boldsymbol{F}_{i} = -\nabla E = -\left(\frac{\partial E}{\partial x_{i}}, \frac{\partial E}{\partial y_{i}}, \frac{\partial E}{\partial z_{i}}\right)$$

Deep Potential Molecular Dynamics (DPMD):



 MD computes the half-step velocities of the atoms according to the forces and simulation time step Δt:

$$\boldsymbol{v}_i\left(t + \frac{\Delta t}{2}\right) = \boldsymbol{v}_i(t) + \frac{\Delta t}{2}\boldsymbol{a}_i(t)$$

- Where  $a_i(t) = \frac{F_i(t)}{m_i}$  is the acceleration
- At last, MD computes the atom coordinates and full-step velocities, generating a new frame:

$$\boldsymbol{R}_{i}(t + \Delta t) = \boldsymbol{R}_{i}(t) + \Delta t \boldsymbol{v}_{i}\left(t + \frac{\Delta t}{2}\right)$$
$$\boldsymbol{v}_{i}(t + \Delta t) = \boldsymbol{v}_{i}\left(t + \frac{\Delta t}{2}\right) + \frac{\Delta t}{2}\boldsymbol{a}_{i}(t + \Delta t)$$

 Since each iteration involves QM calculation, AIMD can be extremely time and energy consuming

Deep Potential Molecular Dynamics (DPMD) [1]:



- In the DPMD framework, a set of local orthogonal unit bases {e<sub>x</sub>, e<sub>y</sub>, e<sub>z</sub>} centered in the target atom *i* is constructed:
  - $e_{\chi}$ : parallel to the O-H bond
  - $e_z$ : perpendicular to H-O-H water molecule plane

• 
$$e_y: e_z \times e_x$$

 The relative coordinate of a neighboring atom j can be determined:

$$\boldsymbol{R}_{ij} = x_{ij}\boldsymbol{e}_x + y_{ij}\boldsymbol{e}_y + z_{ij}\boldsymbol{e}_z$$

- The input coordinates of the Neural Network (NN) can be:
  - With both radial and angular information:

$$\boldsymbol{D}_{ij} = \{1/\boldsymbol{R}_{ij}, x_{ij}/\boldsymbol{R}_{ij}^2, y_{ij}/\boldsymbol{R}_{ij}^2, z_{ij}/\boldsymbol{R}_{ij}^2, \}$$

• Or with radial information only:

$$\boldsymbol{D}_{ij} = \left\{ 1/\boldsymbol{R}_{ij} \right\}$$

[1] Zhang, Linfeng, et al. "Deep potential molecular dynamics: a scalable model with the accuracy of quantum mechanics." *Physical review letters* 120.14 (2018): 143001.

Deep Potential Molecular Dynamics (DPMD):



 $D_{ij}$  of empty neighbors are set to 0

- In the DPMD workflow, the relative coordinates  $\{R_{ij}\}_{i=1,2,...}$  are first computed from absolute coordinates R, then converted into  $\{D_{ij}\}_{i=1,2,...}$
- The NN outputs the energy of each atom  $E_i$  and sum them together to obtain the total energy E
- The loss function is defined as a multi-task loss:

$$L = p_{\epsilon} \Delta \epsilon^{2} + \frac{p_{f}}{3N} \sum_{i} |\Delta F_{i}|^{2} + \frac{p_{\xi}}{9} ||\Delta \xi||^{2}$$

- Consists of 3 terms:
  - Energy per atom  $\epsilon$
  - Force on each atom **F**<sub>i</sub>,
  - Virial tensor  $\xi$  (measures internal stress)
- Where factors *p* are loss weight

Deep Potential Molecular Dynamics (DPMD):

- Relaxation: structures are updated iteratively through AIMD, evolving from an unstable structure to a balanced state
- Comparing the interatomic distance distribution after relaxation via both AIMD and DPMD, the obtained balanced structures fit quite well
- Recall that the NN does not directly predict the interatomic distance, exhibiting the convincing accuracy of the deep potential force field



Deep Potential Molecular Dynamics (DPMD):

 Since the time complexity of DPMD is O(N), it tremendously lowers the computation costs, especially for larger systems



Deep Learning DFT Hamiltonian (DeepH) [1]:

Tips about DFT Hamiltonian  $\hat{H}_{DFT}$ :

- Recall that  $\widehat{H}_{\text{DFT}}$  describes the interactions between basis functions  $\{\phi_i\}$
- $\widehat{H}_{\text{DFT}}$  is determined by the structure  $\{\mathcal{R}\}$
- Many observables are deterministically computed from  $\widehat{H}_{\mathrm{DFT}}$
- $\hat{H}_{\rm DFT}$  has to be obtained through computational expensive SCF calculation



[1] Li, He, et al. "Deep-learning density functional theory Hamiltonian for efficient ab initio electronic-structure calculation." *Nature Computational Science* 2.6 (2022): 367-377.

Deep Learning DFT Hamiltonian (DeepH):

Modeling Structure- $\hat{H}_{\rm DFT}$  Relationship || Modeling Structure-Property Relationship



Deep Learning DFT Hamiltonian (DeepH):

**Fundamental Facts:** 

- DFT does support high-accuracy calculation with acceptable expenses for **small systems**
- DFT is NOT suitable for calculating large systems

Key Problem:

• How to learn from small system DFT data and **expand/generalize** to large systems?



Deep Learning DFT Hamiltonian (DeepH):

Challenges:

- 1. Infinite dimension of  $\hat{H}_{\text{DFT}}$  in the extended systems
- 2. SO(3) Rotation Equivariance of  $\hat{H}_{\text{DFT}}$





 $\widehat{H}_{\rm DFT}$ 

Deep Learning DFT Hamiltonian (DeepH):

Important Prior Physics Knowledge: Nearsightedness Principle [1]

• In the many-body system, local electron properties at  $r_0$  does not response to the distant, local perturbing potential w(r') outside a sphere of radius R



[1] Prodan, Emil, and Walter Kohn. "Nearsightedness of electronic matter." *Proceedings of the National Academy of Sciences* 102.33 (2005): 11635-11638.

Deep Learning DFT Hamiltonian (DeepH):

Localized Basis:

- Atomic orbitals
- Interact only when overlapped
- Well-defined rotation transformations



Deep Learning DFT Hamiltonian (DeepH):

Localized Basis: Sparseness

- Only H<sub>ij</sub> between neighboring atoms (within R<sub>C</sub>, determined by the spread of orbitals, few Å) are nonzero Nearsightedness Principle:
- Only information of neighborhood (within  $R_N$ ) should be considered





Deep Learning DFT Hamiltonian (DeepH):

Localized Basis:

- Modeling Hamiltonian blocks from **local interactions**
- Does NOT respond to long-range configurations





Deep Learning DFT Hamiltonian (DeepH):

SE(3) Equivariance vs. Invariance:

- SE(3) (Special Euclidean group in 3D) includes 3 translation transformation and 3 rotation transformation
- SE(3) Invariance:
  - The output does NOT change with the transformation of the input structure



Deep Learning DFT Hamiltonian (DeepH):

SE(3) Equivariance vs. Invariance:

- SE(3) (Special Euclidean group in 3D) includes 3 translation transformation and 3 rotation transformation
- SE(3) Equivariance:
  - The output changes together with the transformation of the input structure



Deep Learning DFT Hamiltonian (DeepH):

SE(3) Equivariance vs. Invariance:

- Invariant quantity: total energy, band gap, ...
- **Equivariant** quantity:  $\widehat{H}_{DFT}$ , force field, ...







Deep Learning DFT Hamiltonian (DeepH):

Global coordinates: rotation transformation



The overlaps between orbitals are misoriented

Deep Learning DFT Hamiltonian (DeepH):

Local coordinates: rotation transformation



#### The overlaps between orbitals remain unchanged

Deep Learning DFT Hamiltonian (DeepH):

Solution to  $\widehat{H}_{DFT}$  equivariance requirement:

- Similar to DPMD
- Local coordinates  $\{\hat{x}', \hat{y}', \hat{z}'\}$  for bond AB:

$$\hat{x}' = \frac{\boldsymbol{e}_1}{\boldsymbol{e}_1}, \hat{y}' = \frac{\boldsymbol{e}_1 \times \boldsymbol{e}_2}{|\boldsymbol{e}_1 \times \boldsymbol{e}_2|}, \hat{z}' = \hat{x}' \times \hat{y}'$$

• 
$$\boldsymbol{e}_1 = \mathbf{r}_{\mathrm{BA}}$$

- $e_2$ : second nearest  $\mathbf{r}_{\mathrm{kA}}$  non-parallel to  $e_1$
- Ensure the  $\widehat{H}_{DFT}$  element invariant to rotation:

$$t_1 = t_2$$

•  $p_{x'}, p_{z'}: p$  orbitals of different angular momentum quantum numbers

 $\mathbf{e}_1 = \mathbf{r}_{\mathsf{BA}}$  $\mathbf{e}_2 = \mathbf{r}_{\mathsf{CA}}$  $= \mathbf{r}_{\mathsf{BA}}$  $p_{x'}$  $\mathbf{e}_2 = \mathbf{r}_{\mathsf{CA}}$  $H'_{\mathsf{A}p_{x'},\mathsf{B}p_{z'}}$  $p_{x'}$  $H'_{\mathsf{A}p_{x'},\mathsf{B}p}$ 

Deep Learning DFT Hamiltonian (DeepH):

Solution to  $\widehat{H}_{DFT}$  equivariance requirement:

• The rotation transformation from DFT global coordinates to local coordinates of bond AB:

$$R^{AB} = (\hat{x}', \hat{y}', \hat{z}')$$

- with  $\hat{x}', \hat{y}', \hat{z}'$  being column vectors
- And  $\hat{H}'_{DFT}$  under **local coordinates** can be obtained for training:

$$H_{A\alpha,B\beta}' = \sum_{a,b} D_{\alpha,a}^{l_{\alpha}} (R^{AB}) H_{A\alpha,B\beta} D_{b,\beta}^{l_{\beta}} ((R^{AB})^{-1})$$

- where  $D^{(l)}$  is the Wigner matrix, and  $l_{\alpha}$  is angular momentum quantum number of the orbital  $\alpha$
- The predicted  $\hat{H}'_{DFT}$  is transformed back to **global coordinates** to preserve **equivariance**:

$$H_{A\alpha,B\beta} = \sum_{a,b} D_{\alpha,a}^{l_{\alpha}} \left( (R^{AB})^{-1} \right) H_{A\alpha,B\beta}' D_{b,\beta}^{l_{\beta}} (R^{AB})$$

Deep Learning DFT Hamiltonian (DeepH):

Crystal graph: consists of vertices  $v_i$  and edges  $e_{ij}$  within cutoff radius  $R_C$ An edge is added between two atoms if the orbitals are overlapped



Deep Learning DFT Hamiltonian (DeepH):



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Deep Learning DFT Hamiltonian (DeepH):

LCMP Layer: relative orientation information  $\hat{\mathbf{r}}_{ik}^{pq}$  of bond ik under local coordinate defined for edge pq is added into the initial edge features, and predict Hamiltonian element  $\hat{H}_{i\alpha,j\beta}$ 





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Deep Learning DFT Hamiltonian (DeepH):

Performance: trained and tested on graphene 6x6 supercell MD data (containing a variety of configurations)


Deep Learning DFT Hamiltonian (DeepH):

Performance: generalization for 2,000 unseen graphene configurations



Density of State (DOS): distribution of electrons of different energy states Shift current conductivity  $\sigma^{yyy}$ : conductivity of electrons excited by photons of different energy  $\omega$ 

Deep Learning DFT Hamiltonian (DeepH):

Generalization Performance: trained on flat sheet graphene, tested on curved carbon nanotubes



Deep Learning DFT Hamiltonian (DeepH):

Generalization Performance: moiré-twisted bilayer materjals





1.08  $^\circ$  magic angle graphene: **11,164** carbon atoms per unit cell

Deep Learning DFT Hamiltonian (DeepH):

Generalization Performance: moiré-twisted bilayer materials



trained on **non-twisted small** bilayer structures tested on **twisted large** structures Linear complexity for large systems

Deep Learning DFT Hamiltonian (DeepH):

Generalization Performance: trained on non-twisted small bilayer structures, tested on twisted large



# Al in Materials Science

**Directly Bridging** 

## Deep Learning Approaches: CGCNN

Crystal Graph Convolutional Neural Networks (CGCNN) [1]:

Directly bridging the gap between crystal structures and material properties via GNN Construction of crystal graph:

- Node  $v_i$  representing physical properties of atom i
- Edge  $e_{(i,j)_k}$  representing the distance between atom *i* and its k-th nearest neighbor *j*



[1] Xie, Tian, and Jeffrey C. Grossman. "Crystal graph convolutional neural networks for an accurate and interpretable prediction of material properties." *Physical review letters* 120.14 (2018): 145301.

## Deep Learning Approaches: CGCNN

Crystal Graph Convolutional Neural Networks (CGCNN):

The node feature is updated following:

$$v_i^{(t+1)} = v_i^{(t)} + \sum_{j,k} \sigma \left( z_{(i,j)_k}^{(t)} W_f^{(t)} + b_f^{(t)} \right) \bigcirc g \left( z_{(i,j)_k}^{(t)} W_s^{(t)} + b_s^{(t)} \right)$$

Where

$$z_{(i,j)_k}^{(t)} = v_i^{(t)} \oplus v_j^{(t)} \oplus e_{(i,j)_k}$$

And node features are pooled for global properties prediction



 $\odot$ : element-wise production,  $\oplus$ : concatenation

#### Deep Learning Approaches: CGCNN

Crystal Graph Convolutional Neural Networks (CGCNN):



# Al in Materials Science

**Inverse Problem** 

#### Next Level: Inverse Problem

#### Can we start with the desired properties?



#### Next Level: Inverse Problem

Denoising Diffusion Probabilistic Models (DDPM) (Lecture 3):

- Mapping unknown data distribution to a known prior distribution (e.g. standard Gaussian)
- Making effective sampling from the original data distribution feasible



Gaussian distribution

data distribution

Crystal Diffusion Variational AutoEncoder (CDVAE) [1]:



[1] Xie, Tian, et al. "Crystal diffusion variational autoencoder for periodic material generation." *arXiv preprint arXiv:2110.06197* (2021).

Crystal Diffusion Variational AutoEncoder (CDVAE): Training:

- Encode crystal structure M into latent representation z with a periodic graph neural network PGNN<sub>ENC</sub>
- Decode crystal aggregation properties (*c*, *L*, *N*) through MLP<sub>AGG</sub>
- Denoise corrupted structure  $\widetilde{M} = (\widetilde{A}, \widetilde{X}, L)$  conditioned on  $\boldsymbol{z}$  through PGNN<sub>DEC</sub>



Crystal Diffusion Variational AutoEncoder (CDVAE): Generation:

- Sample a latent representation  $z \sim \mathcal{N}(0,1)$
- Decode crystal aggregation properties (c, L, N) through MLP<sub>AGG</sub>
- Randomly initialize a disordered crystal structure  $\widetilde{M}$  according to (c, L, N)
- Denoise corrupted structure  $\widetilde{M} = (\widetilde{A}, \widetilde{X}, L)$  conditioned on  $\boldsymbol{z}$  through PGNN<sub>DEC</sub>



Crystal Diffusion Variational AutoEncoder (CDVAE): Property optimization:

- Jointly trained property predictor:  $\tilde{P} = F_{MLP}(z)$
- Optimize latent using back propagation (BP) for 5,000 steps
- Decode 10 crystal structures every 500 steps from the latent trajectory
- Select one best structure with closest  $\tilde{P}$  predicted by an individual predictor



MatterGen [1]: Tailored diffusion process for crystalline materials:

 $q(\mathbf{A}_{t+1}, \mathbf{X}_{t+1}, \mathbf{L}_{t+1} | \mathbf{A}_t, \mathbf{X}_t, \mathbf{L}_t) = q(\mathbf{A}_{t+1} | \mathbf{A}_t) q(\mathbf{X}_{t+1} | \mathbf{X}_t) q(\mathbf{L}_{t+1} | \mathbf{L}_t)$ 

• Atom types: 
$$\boldsymbol{A} = (\boldsymbol{a}_1, \boldsymbol{a}_2, \dots, \boldsymbol{a}_N) \in \mathbb{A}^N$$

- Atom fractional coordinates:  $X = (x_1, x_2, ..., x_N) \in [0, 1)^{N \times 3}$
- Lattice:  $\boldsymbol{L} = (\boldsymbol{l}_1, \boldsymbol{l}_2, \boldsymbol{l}_3) \in \mathbb{R}^{3 \times 3}$

MatterGen:

Tailored diffusion process for crystalline materials:

• Atom type *A*:

$$q(\boldsymbol{a}_t | \boldsymbol{a}_{t-1}) = \operatorname{Cat}(\boldsymbol{a}_t; \boldsymbol{p} = \boldsymbol{a}_{t-1} \boldsymbol{Q}_t)$$

- Cat(a; p): categorical distribution over 1-hot vectors whose probabilities are given by the row vector p
- $[\mathbf{Q}_t]_{ij} = q(a_t = j | a_{t-1} = i)$ : Markov transition matrix at time step t

$$[\mathbf{Q}_t]_{ij} = \begin{cases} 1 & i = j = m \\ 1 - \beta_t & i = j \neq m \\ \beta_t & j = m \neq i \\ 0 & m \neq i \neq j \neq m \end{cases}$$

- $\beta_t$ : probability of transiting to a **MASK** state
- $1 \beta_t$ : probability of staying unchanged

MatterGen:

Tailored diffusion process for crystalline materials:

• Fractional coordinates X:

$$q(\boldsymbol{x}_t | \boldsymbol{x}_0) = \mathcal{N}_W(\boldsymbol{x}_t; \boldsymbol{x}_0, \sigma_t^2 \boldsymbol{I})$$

•  $\mathcal{N}_W$ : wrapped normal distribution preserving periodic boundary condition (PBC)

$$\mathcal{N}_{W}(\boldsymbol{x}_{t};\boldsymbol{x}_{0},\sigma_{t}^{2}\boldsymbol{I}) = \sum_{\boldsymbol{k}\in\mathbb{Z}^{3}}\mathcal{N}(\boldsymbol{x}_{t};\boldsymbol{x}_{0}-\boldsymbol{k},\sigma_{t}^{2}\boldsymbol{I})$$

MatterGen:

Tailored diffusion process for crystalline materials:

- Lattice *L*:
- Naïve diffusion process:

$$q(\boldsymbol{L}_t|\boldsymbol{L}_0) = \mathcal{N}(\sqrt{\overline{\alpha}_t}\boldsymbol{L}_0, (1-\overline{\alpha}_t)\boldsymbol{I})$$

- Leads to extremely narrow and small lattices
- Custom limiting mean & variance:

$$q(\boldsymbol{L}_t|\boldsymbol{L}_0) = \mathcal{N}(\sqrt{\bar{\alpha}_t}\boldsymbol{L}_0 + (1 - \sqrt{\bar{\alpha}_t})\boldsymbol{\mu}(n)\boldsymbol{I}, (1 - \bar{\alpha}_t)\sigma_t^2(n)\boldsymbol{I})$$

• which yields the limit distribution for  $T \rightarrow \infty$ :

$$q(\boldsymbol{L}_T) = \mathcal{N}(\mu(n)\boldsymbol{I}, \sigma_T^2(n)\boldsymbol{I})$$

- where  $\mu(n) = \sqrt[3]{nc}$ ,  $\sigma_T^2(n) = \sqrt[3]{nv}$
- *c*: inverse average atomic density of the dataset
- *v*: average unit cell volume of the dataset
- The signal-to-noise-ratio at T is therefore independent to the number of atoms n:

$$SNR = \lim_{T \to \infty} \frac{|\mu(n)|}{\sigma(n)} = \sqrt[3]{\frac{c}{v}}$$

MatterGen:

Tailored diffusion process for crystalline materials:



MatterGen:

Conditional generation of materials:



Fine-tuned for different tasks with a **frozen base model** 

# Al in Materials Science

Al as a Powerful Assistance

#### Al as a Powerful Assistance:





Transmission Electron Microscopy (TEM)



Scanning Tunneling Microscopy (STM)

#### **Analysis & Interpretation**



Crystal structure

Single crystal Si





## Al as a Powerful Assistance: CrySTINe

Crystal Structure-Type Identification Network (CrySTINet) [1]:



Input the XRD pattern of an unknown compound

Choose the **most probable structure type** as the final result

[1] Chen, Litao, et al. "Crystal Structure Assignment for Unknown Compounds from X-ray Diffraction Patterns with Deep Learning." *Journal of the American Chemical Society* 146.12 (2024): 8098-8109.

## Al as a Powerful Assistance: CrySTINe

Crystal Structure-Type Identification Network (CrySTINet):



Cosine similarity as an extra criterion

4-D Scanning Transmission Electron Microscopy (4D-STEM) :

- Each pixel in real-space corresponds to a 2-D diffraction pattern
- Each diffraction pattern contains **local structure information** within the *nm* range
- 4D-STEM data can easily reach GBs
- Statistical or computational approaches for interpretation are indispensable



#### 4D-STEM Data Analysis [1]:



#### Hierarchical k-means clustering

#### Features of different scales are clustered sequentially

[1] Kimoto, Koji, et al. "Unsupervised machine learning combined with 4D scanning transmission electron microscopy for bimodal nanostructural analysis." *Scientific Reports* 14.1 (2024): 2901.

4D-STEM Analysis:





Features of different scales are clustered sequentially

4D-STEM Analysis:







GNoME:



GNoME:



Discovered up to 380,000 computationally stable structures never found before



Recipe optimization Phase identification [1] Szymanski, Nathan J., et al. "An autonomous laboratory for the accelerated synthesis of novel materials." *Nature* 624.7990 (2023): 86-91.



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#### Al as a Powerful Assistance: Material Discovery



#### Al as a Powerful Assistance :



# Al in Materials Science

**Outside and Beyond Crystals** 

#### Outside of the Crystals: Amorphous Materials

AI in Polymer Science:

- Input polymer electrolyte structure and formula
- Predicating ionic conductivities  $\sigma$  by predicting pre-exponential factor A and activation energy  $E_a$  in the Arrhenius equation:

$$\ln(\sigma) = \ln(A) - \frac{E_a}{RT}$$



## Beyond Crystals: MetaMaterials

Metamaterials based on prescribed mechanical behavior [1]

- Mechanical properties determined by mm scale topology (10 mm unit cell)
- Inverse design of topology structure with the target compressive behavior in the form of curve features



[1] Ha, Chan Soo, et al. "Rapid inverse design of metamaterials based on prescribed mechanical behavior through machine learning." Nature Communications 14.1 (2023): 5765.

## Beyond Crystals: MetaMaterials

Shape-programmable 3D kirigami metamaterials [1]

• Inverse design of cut layout with the desired deformation





[1] Alderete, Nicolas A., Nibir Pathak, and Horacio D. Espinosa. "Machine learning assisted design of shape-programmable 3D kirigami metamaterials." npj 114 Computational Materials 8.1 (2022): 191.

## Useful Resources:

- A Tutorial on Density Functional Theory: <u>https://www.researchgate.net/publication/226474665\_A\_Tutorial\_on\_Density\_Functional\_Theory</u>
- Material Project: <u>https://next-gen.materialsproject.org/</u>
- MP Seminar Inverse Design: Why Aren't We There Yet?: https://youtu.be/0I07QNAexRc?si=EaNuCcuwwDIDfBxM
- MP Seminar MatterGen: <u>https://youtu.be/Smz1go6\_Spo?si=xnU8kXWNFVIYf-Zf</u>

#### Additional materials

# Physical properties derived from the DFT Hamiltonian

- Band structure and DOS:
  - The eigenvalues  $\varepsilon_{nk}$  and eigenstates  $v_{nk}$  of the Hamiltonian  $\widehat{H}$  at band n and wavevector k can be obtained by solving the generalized eigenvalue problem:  $H(k)v_{nk} = \varepsilon_{nk}S(k)v_{nk}$
  - where the overlap matrix S is obtained by the inner product of the basis at very low computational cost
  - $\varepsilon_{nk}$  of at band n and wavevector k construct the band structure
  - DOS is obtained by integrating the number of electronic in momentum space in the band structure over each value of energy:

$$D(E) = \int \delta(E - E(\mathbf{k})) d^3\mathbf{k}$$

# Physical properties derived from the DFT Hamiltonian

• Shift current conductivity  $\sigma^{abc}$ :  $\sigma^{abc}(\omega) = \frac{\pi e^3}{\hbar^2} \int \frac{d^3 \mathbf{k}}{(2\pi)^3} \times \sum_{n,m} f_{nm} \operatorname{Im}(r_{mn}^b r_{nm}^{c,a} + r_{mn}^c r_{nm}^{b,a}) \delta(\omega_{mn}(\mathbf{k}) - \omega)$ 

• 
$$\omega_{mn}(\mathbf{k}) = \frac{E_{nk} - E_{mk}}{\hbar}$$
: difference of energy eigenvalues

- $f_{nm} = f_n(\mathbf{k}) f_m(\mathbf{k})$ : Fermi–Dirac occupations of bands n and m at wavevector  $\mathbf{k}$
- $r_{mn}^{a}$  and  $r_{nm}^{b,a} = \frac{\partial r_{nm}^{b}}{\partial k^{a}} i(r_{nn}^{a} r_{mm}^{a})r_{nm}^{b}$  are Berry connection and its general derivative, calculated with the DFT Hamiltonian using the method developed in ref [1]

[1] Wang, Chong, et al. "First-principles calculation of optical responses based on nonorthogonal localized orbitals." *New Journal of Physics* 21.9 (2019): 093001.